

Applications

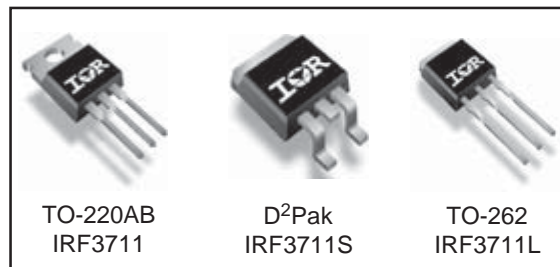
- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use
- High Frequency Buck Converters for Server Processor Power Synchronous FET
- Optimized for Synchronous Buck Converters Including Capacitive Induced Turn-on Immunity

Benefits

- Ultra-Low Gate Impedance
- Very Low RDS(on) at 4.5V V_{GS}
- Fully Characterized Avalanche Voltage and Current

HEXFET® Power MOSFET

V_{DSS}	R_{DS(on)} max	I_D
20V	6.0mΩ	110A[Ⓒ]



Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V _{DS}	Drain-Source Voltage	20	V
V _{GS}	Gate-to-Source Voltage	± 20	V
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	110 [Ⓒ]	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	69	
I _{DM}	Pulsed Drain Current [Ⓓ]	440	
P _D @ T _C = 25°C	Maximum Power Dissipation	120	W
P _D @ T _A = 25°C	Maximum Power Dissipation [Ⓔ]	3.1	W
	Linear Derating Factor	0.96	W/°C
T _J , T _{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	1.04	°C/W
R _{θCS}	Case-to-Sink, Flat, Greased Surface [Ⓓ]	0.50	—	
R _{θJA}	Junction-to-Ambient [Ⓓ]	—	62	
R _{θJA}	Junction-to-Ambient (PCB mount) [Ⓔ]	—	40	

Notes [Ⓓ] through [Ⓔ] are on page 11

IRF3711/3711S/3711L

International
IR Rectifier

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	20	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.022	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	4.7	6.0	m Ω	$V_{GS} = 10V, I_D = 15A$ ③
		—	6.2	8.5		$V_{GS} = 4.5V, I_D = 12A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	3.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 16V, V_{GS} = 0V$
		—	—	100		$V_{DS} = 16V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -16V$

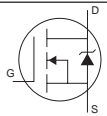
Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	53	—	—	S	$V_{DS} = 16V, I_D = 30A$
Q_g	Total Gate Charge	—	29	44	nC	$I_D = 15A$
Q_{gs}	Gate-to-Source Charge	—	7.3	—		$V_{DS} = 10V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	8.9	—		$V_{GS} = 4.5V$
Q_{oss}	Output Gate Charge	—	33	—		$V_{GS} = 0V, V_{DS} = 10V$
$t_{d(on)}$	Turn-On Delay Time	—	12	—	ns	$V_{DD} = 10V$
t_r	Rise Time	—	220	—		$I_D = 30A$
$t_{d(off)}$	Turn-Off Delay Time	—	17	—		$R_G = 1.8\Omega$
t_f	Fall Time	—	12	—		$V_{GS} = 4.5V$ ③
C_{iss}	Input Capacitance	—	2980	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	1770	—		$V_{DS} = 10V$
C_{rss}	Reverse Transfer Capacitance	—	280	—		$f = 1.0\text{MHz}$

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	460	mJ
I_{AR}	Avalanche Current①	—	30	A

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	110⑥	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	440		
V_{SD}	Diode Forward Voltage	—	0.88	1.3	V	$T_J = 25^\circ\text{C}, I_S = 30A, V_{GS} = 0V$ ③
		—	0.82	—		$T_J = 125^\circ\text{C}, I_S = 30A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	50	75	ns	$T_J = 25^\circ\text{C}, I_F = 16A, V_R = 10V$
Q_{rr}	Reverse Recovery Charge	—	61	92	nC	$di/dt = 100A/\mu s$ ③
t_{rr}	Reverse Recovery Time	—	48	72	ns	$T_J = 125^\circ\text{C}, I_F = 16A, V_R = 10V$
Q_{rr}	Reverse Recovery Charge	—	65	98	nC	$di/dt = 100A/\mu s$ ③

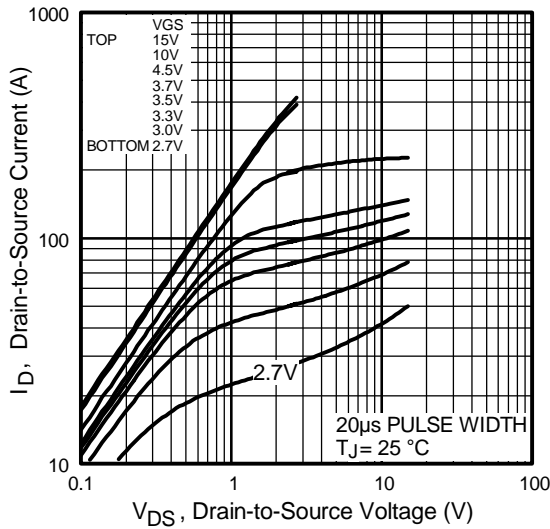


Fig 1. Typical Output Characteristics

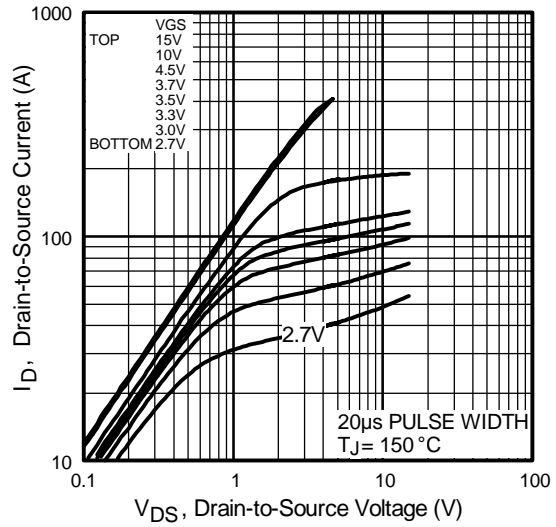


Fig 2. Typical Output Characteristics

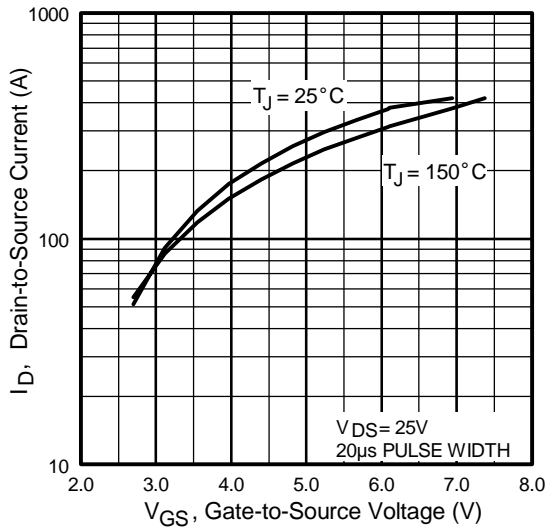


Fig 3. Typical Transfer Characteristics

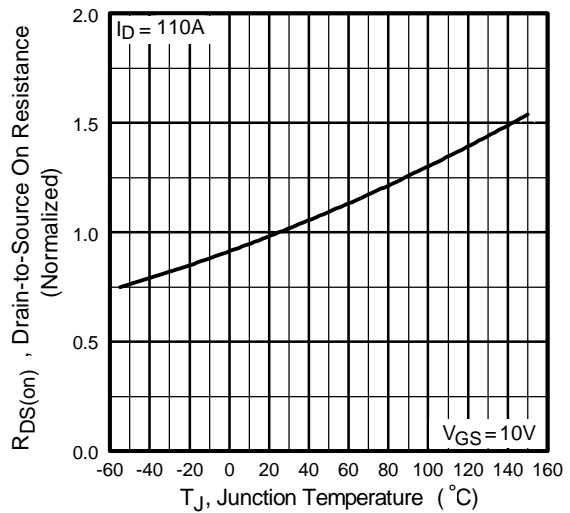


Fig 4. Normalized On-Resistance Vs. Temperature

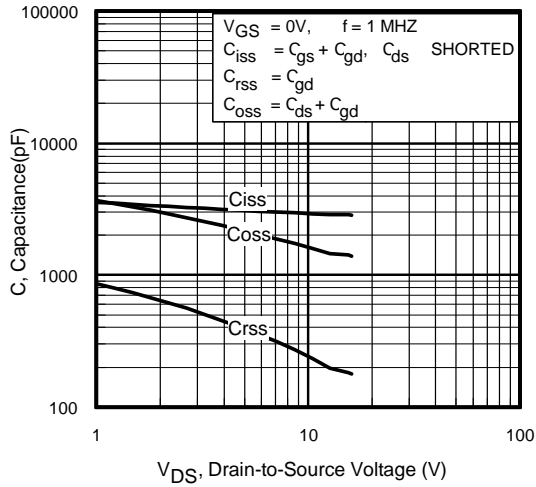


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

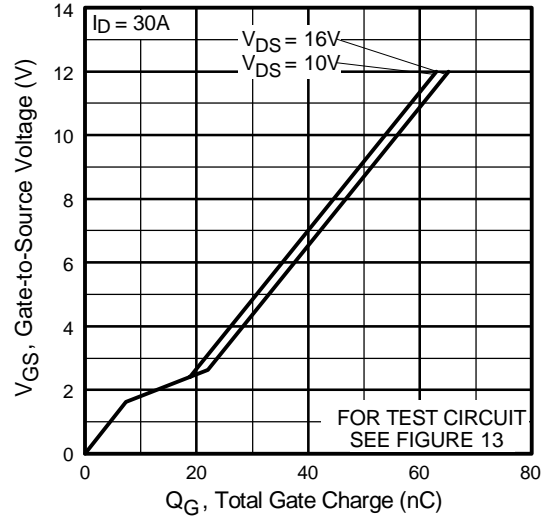


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

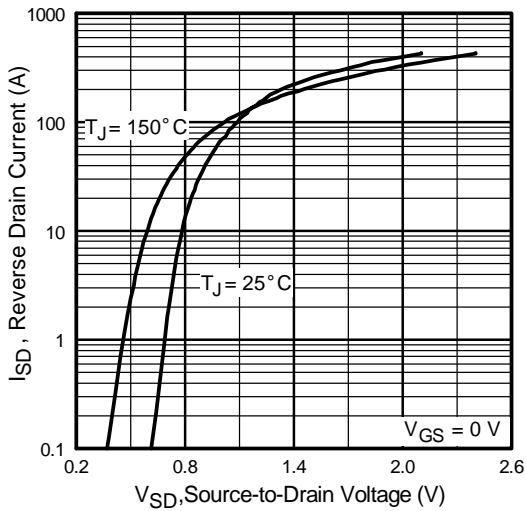


Fig 7. Typical Source-Drain Diode Forward Voltage

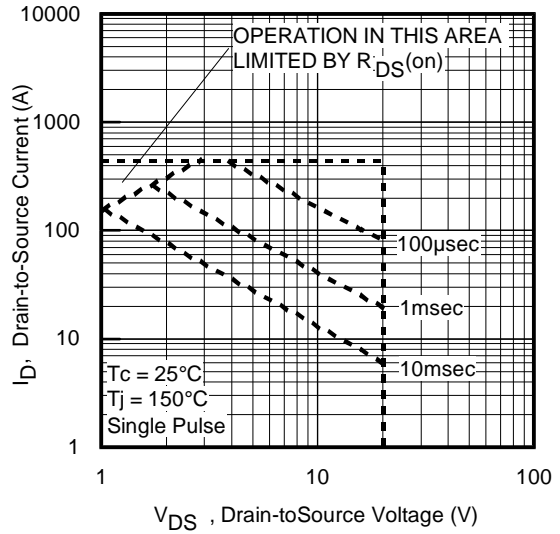


Fig 8. Maximum Safe Operating Area

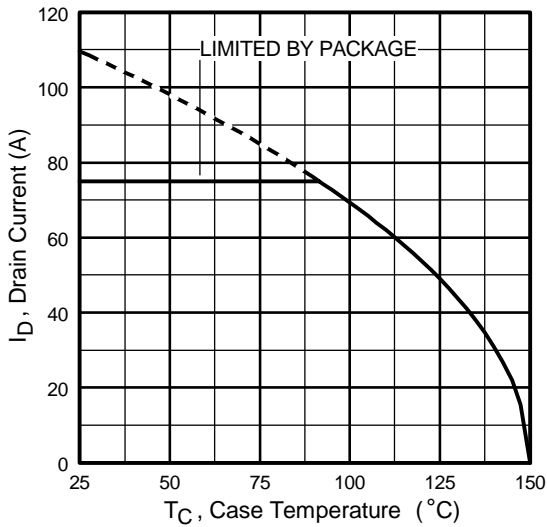


Fig 9. Maximum Drain Current Vs. Case Temperature

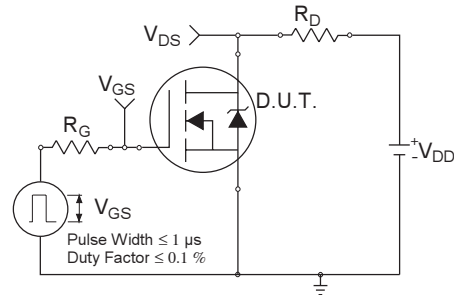


Fig 10a. Switching Time Test Circuit

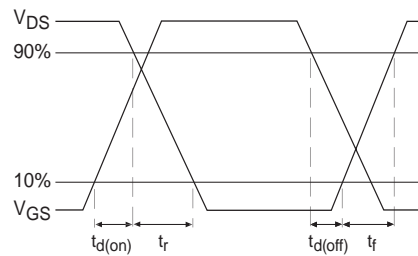


Fig 10b. Switching Time Waveforms

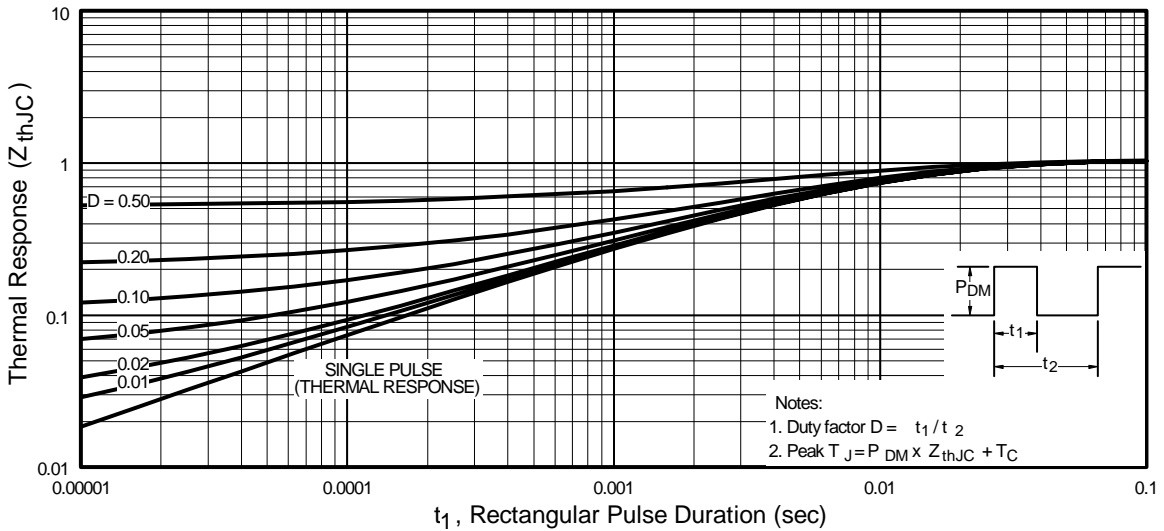


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

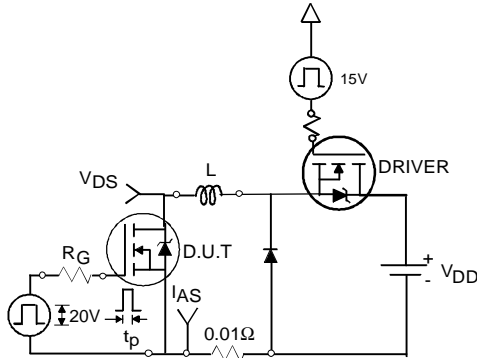


Fig 12a. Unclamped Inductive Test Circuit

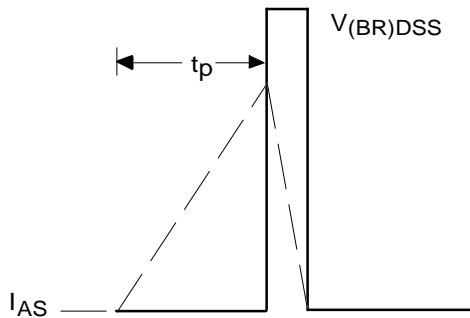


Fig 12b. Unclamped Inductive Waveforms

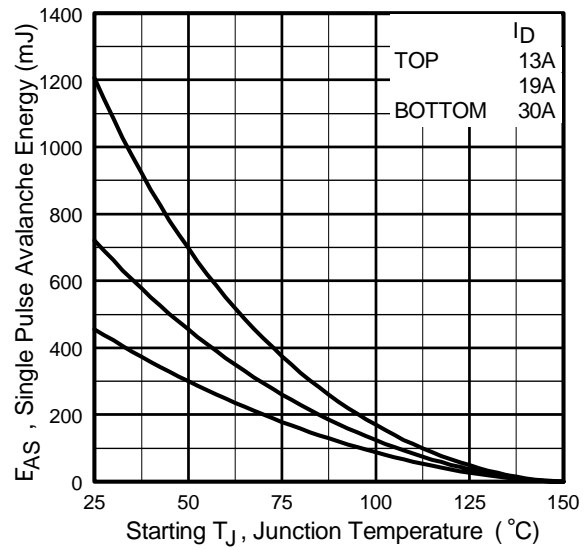


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

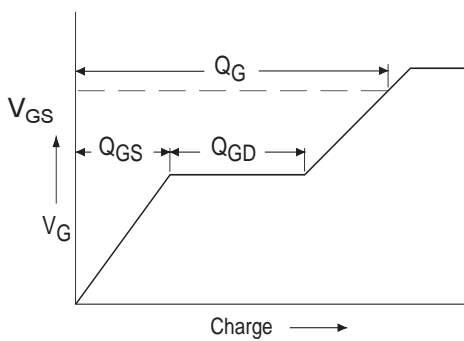


Fig 13a. Basic Gate Charge Waveform

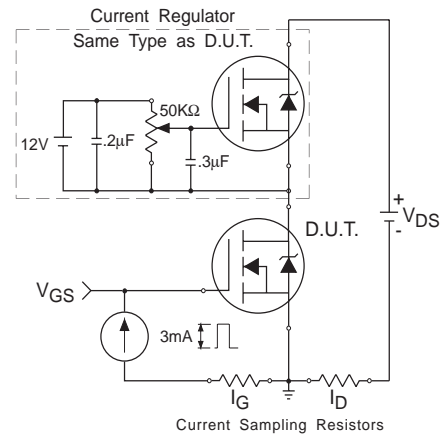
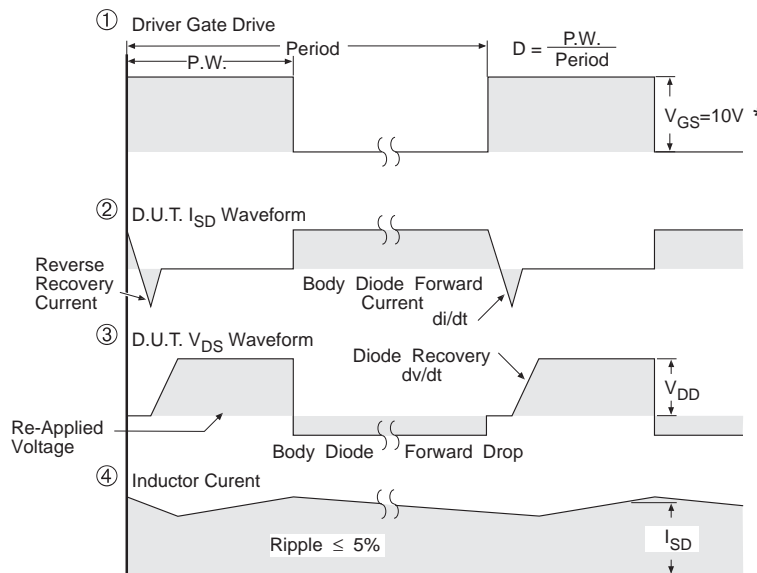
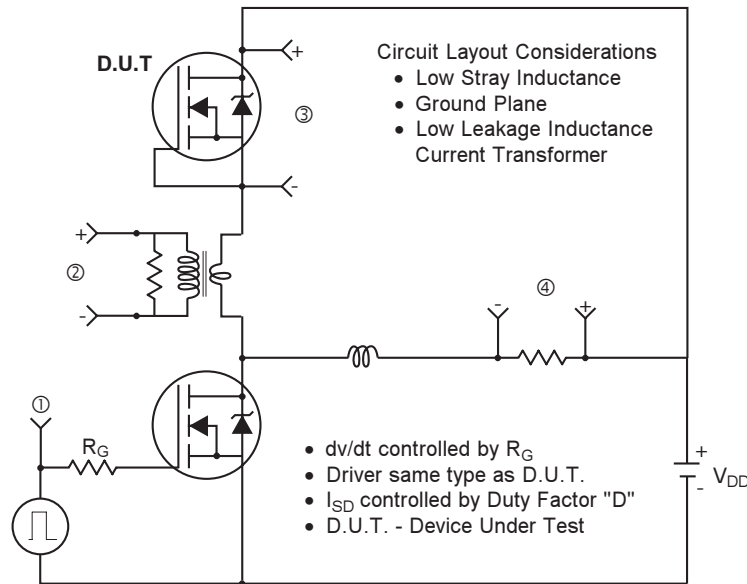


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

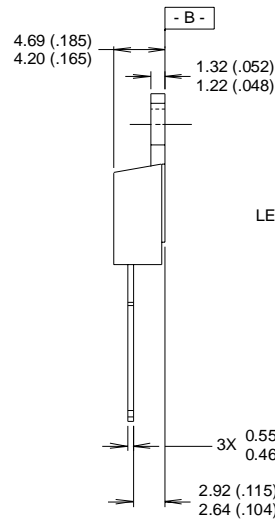
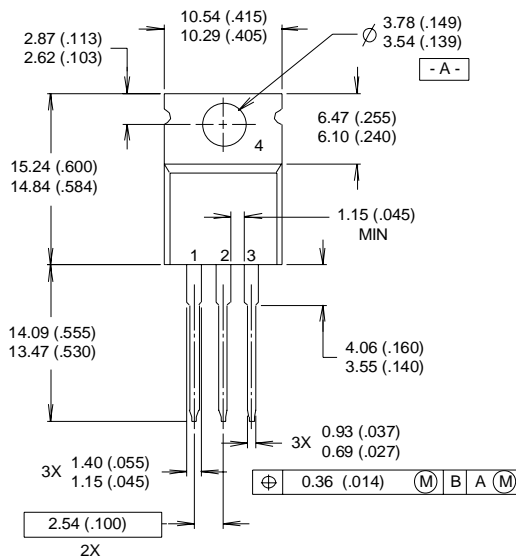
Fig 14. For N-Channel HEXFET® Power MOSFETs

IRF3711/3711S/3711L

International
IR Rectifier

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



LEAD ASSIGNMENTS
1 - GATE
2 - DRAIN
3 - SOURCE
4 - DRAIN

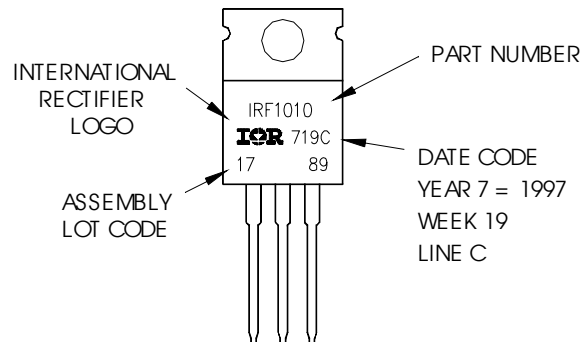
NOTES:

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH

- 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
- 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

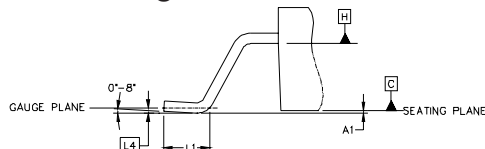
TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

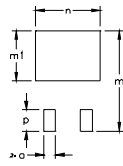
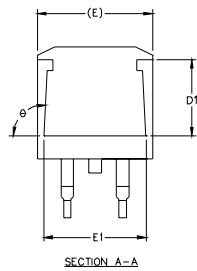
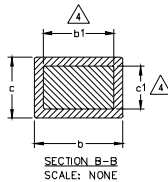


D²Pak Package Outline

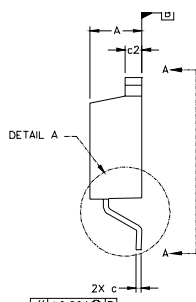
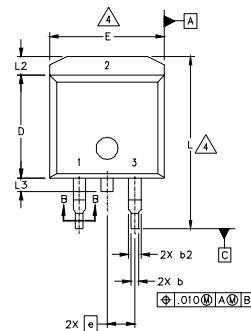
IRF3711/3711S/3711L



DETAIL "A"
 ROTATED 90°
 SCALE 8:1



FOOT PRINT
 SCALE 2:1



SYMBOL	DIMENSIONS				NOTES	
	MILLIMETERS		INCHES			
	MIN.	MAX.	MIN.	MAX.		
A	4.06	4.83	.160	.190	4	
A1		0.127		.005		
b	0.51	0.99	.020	.039		
b1	0.51	0.89	.020	.035		
b2	1.14	1.40	.045	.055		
c	0.38	0.74	.015	.029		
c1	0.43	0.63	.017	.025		4
c2	1.14	1.40	.045	.055		
D	8.51	9.65	.335	.380		3
D1	5.33		.210			
E	9.65	10.67	.380	.420	3	
E1	6.22		.245			
e	2.54 BSC		.100 BSC			
L	14.61	15.88	.575	.625		
L1	1.78	2.79	.070	.110		
L2		1.65		.065		
L3	1.27	1.78	.050	.070		
L4	0.25 BSC		.010 BSC			
m	17.78		.700			
m1	8.89		.350			
n	11.43		.450			
o	2.08		.082			
p	3.81		.150			
θ	90°	93°	90°	93°		

LEAD ASSIGNMENTS

HEXFET	IGBTs, CoPACK	DIODES
1.- GATE	1.- GATE	1.- ANODE *
2.- DRAIN	2.- COLLECTOR	2.- CATHODE
3.- SOURCE	3.- EMITTER	3.- ANODE

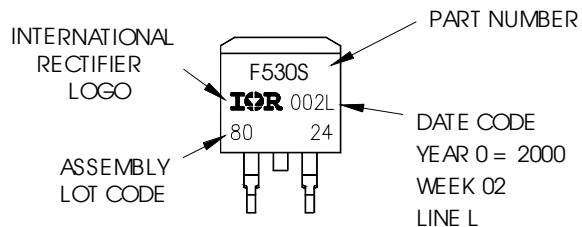
* PART DEPENDENT.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

D²Pak Part Marking Information

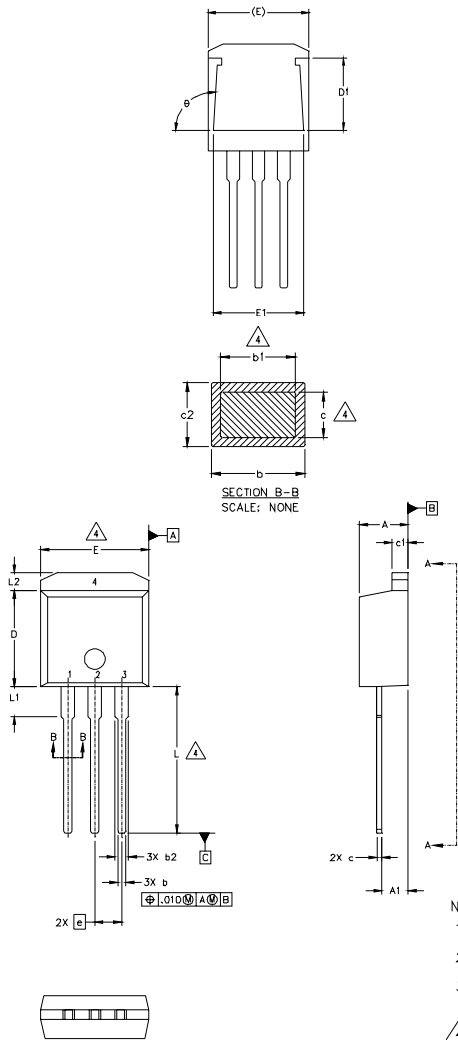
EXAMPLE: THIS IS AN IRF530S WITH
 LOT CODE 8024
 ASSEMBLED ON WW 02, 2000
 IN THE ASSEMBLY LINE "L"



IRF3711/3711S/3711L

International
IR Rectifier

TO-262 Package Outline



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.40	.045	.055	
c	0.38	0.63	.015	.025	4
c1	1.14	1.40	.045	.055	
c2	0.43	.063	.017	.029	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

LEAD ASSIGNMENTS

HEXFET

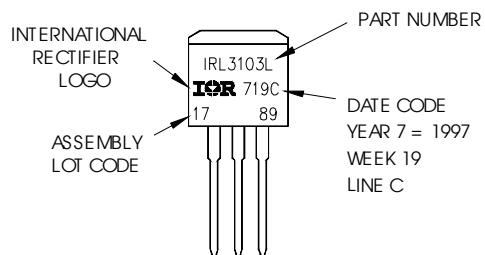
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

NOTES:

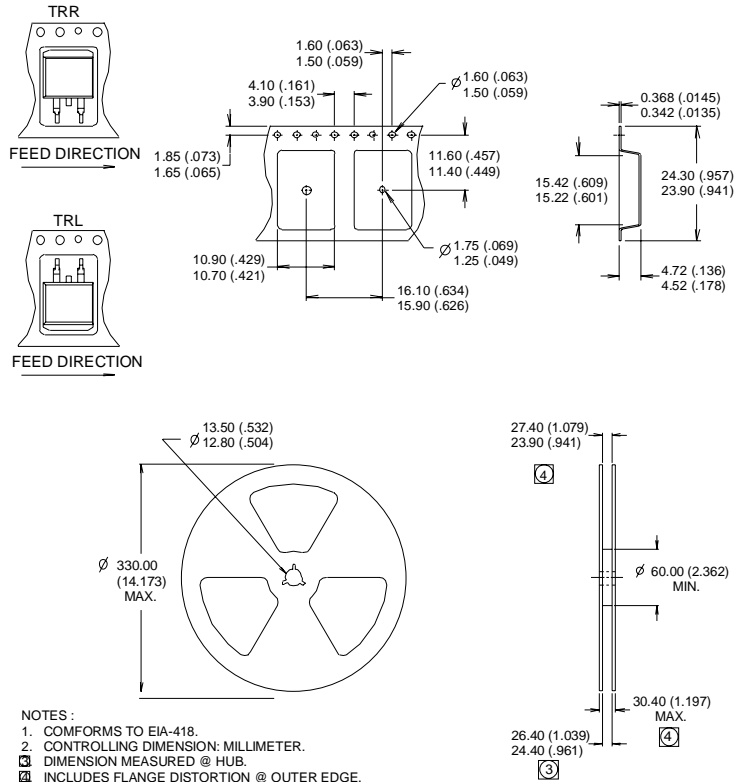
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [".005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"



D²Pak Tape & Reel Information



Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 1.0\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 30\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ This is only applied to TO-220AB package.
- ⑤ This is applied to D²Pak, when mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑥ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.

Data and specifications subject to change without notice.
 This product has been designed and qualified for the industrial market.
 Qualification Standards can be found on IR's Web site.



LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

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